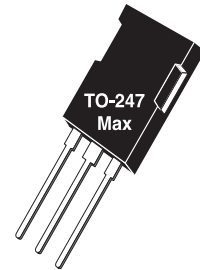



Thunderbolt IGBT®

The Thunderbolt IGBT® is a new generation of high voltage power IGBTs. Using Non-Punch-Through Technology, the Thunderbolt IGBT® offers superior ruggedness and ultrafast switching speed.


Features

- Low Forward Voltage Drop
- Low Tail Current
- RoHS Compliant 
- RBSOA and SCSOA Rated
- High Frequency Switching to 50KHz
- Ultra Low Leakage Current

Unless stated otherwise, Microsemi discrete IGBTs contain a single IGBT die. This device is made with two parallel IGBT die. It is intended for switch-mode operation. It is not suitable for linear mode operation.

Maximum Ratings

 All Ratings: $T_C = 25^\circ C$ unless otherwise specified.

Symbol	Parameter	Ratings	Unit
V_{CES}	Collector-Emitter Voltage	1200	Volts
V_{GE}	Gate-Emitter Voltage	± 30	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ C$	94	Amps
I_{C2}	Continuous Collector Current @ $T_C = 100^\circ C$	50	
I_{CM}	Pulsed Collector Current ^①	150	
SSOA	Switching Safe Operating Area @ $T_j = 150^\circ C$	150A @ 1200V	
P_D	Total Power Dissipation	625	Watts
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ C$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

Static Electrical Characteristics

Symbol	Characteristic / Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 3mA$)	1200	-	-	Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 2mA, T_j = 25^\circ C$)	4.5	5.5	6.5	
$V_{CE(ON)}$	Collector Emitter On Voltage ($V_{GE} = 15V, I_C = 50A, T_j = 25^\circ C$)	2.7	3.2	3.7	
	Collector Emitter On Voltage ($V_{GE} = 15V, I_C = 50A, T_j = 125^\circ C$)	-	4.0	-	
I_{CES}	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_j = 25^\circ C$) ^②	-	-	300	μA
	Collector Cut-off Current ($V_{CE} = 1200V, V_{GE} = 0V, T_j = 125^\circ C$) ^②	-	-	TBD	
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V$)	-	-	300	nA



CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Dynamic Characteristic
APT50GT120B2RDQ2R

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V, V_{CE} = 25V$ $f = 1MHz$	-	3700	-	pF
C_{oes}	Output Capacitance		-	380	-	
C_{res}	Reverse Transfer Capacitance		-	225	-	
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 600V$ $I_C = 50A$	-	10.5	-	V
Q_g	Total Gate Charge		-	340	-	nC
Q_{ge}	Gate-Emitter Charge		-	40	-	
Q_{gc}	Gate-Collector Charge		-	210	-	
SSOA	Switching Safe Operating Area	$T_J = 150^\circ C, R_G = 1.0\Omega^{(2)}, V_{GE} = 15V,$ $L = 100\mu H, V_{CE} = 1200V$	150			A
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (25°C) $V_{CC} = 800V$ $V_{GE} = 15V$ $I_C = 50A$ $R_G = 4.7\Omega$ $T_J = +25^\circ C$	-	24	-	ns
t_r	Current Rise Time		-	53	-	
$t_{d(off)}$	Turn-Off Delay Time		-	230	-	
t_f	Current Fall Time		-	26	-	μJ
E_{on1}	Turn-On Switching Energy ⁽⁴⁾		-	TBD	-	
E_{on2}	Turn-On Switching Energy ⁽⁵⁾		-	5330	-	
E_{off}	Turn-Off Switching Energy ⁽⁶⁾	-	2033	-		
$t_{d(on)}$	Turn-On Delay Time	Inductive Switching (125°C) $V_{CC} = 800V$ $V_{GE} = 15V$ $I_C = 50A$ $R_G = 4.7\Omega$ $T_J = 125^\circ C$	-	24	-	ns
t_r	Current Rise Time		-	53	-	
$t_{d(off)}$	Turn-Off Delay Time		-	255	-	
t_f	Current Fall Time		-	48	-	μJ
E_{on1}	Turn-On Switching Energy ⁽⁴⁾		-	TBD	-	
E_{on2}	Turn-On Switching Energy ⁽⁵⁾		-	5670	-	
E_{off}	Turn-Off Switching Energy ⁽⁶⁾	-	2850	-		

Thermal and Mechanical Characteristics

Symbol	Characteristic / Test Conditions	Min	Typ	Max	Unit
$R_{\theta JC}$	Junction to Case (IGBT)			0.20	°C/W
$R_{\theta JC}$	Junction to Case (DIODE)			0.80	
W_T	Package Weight		6.2		g

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices, I_{ces} includes both IGBT and FRED leakages.

③ See MIL-STD-750 Method 3471.

④ E_{on1} is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to z a the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.

⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

⑦ R_G is external gate resistance not including gate driver impedance.

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

Typical Performance Curves

APT50GT120B2RDQ2G

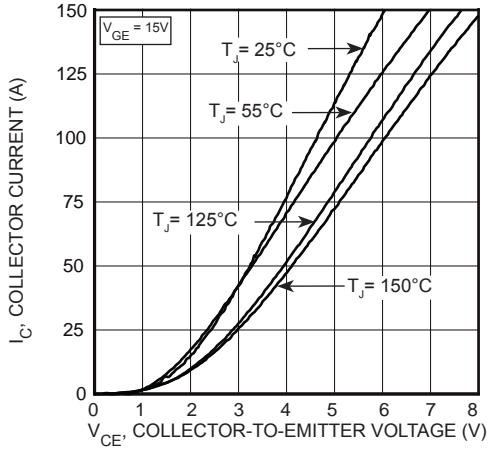


FIGURE 1, Output Characteristics ($T_J = 25^\circ\text{C}$)

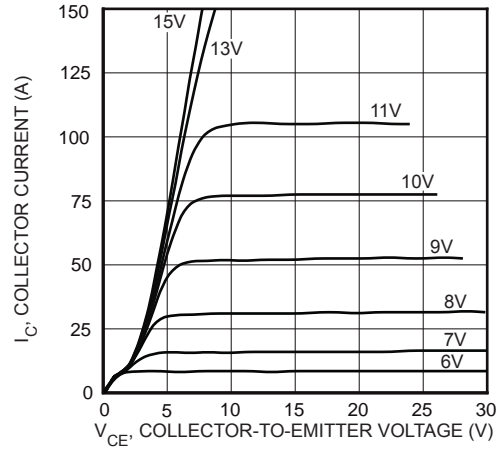


FIGURE 2, Output Characteristics ($T_J = 25^\circ\text{C}$)

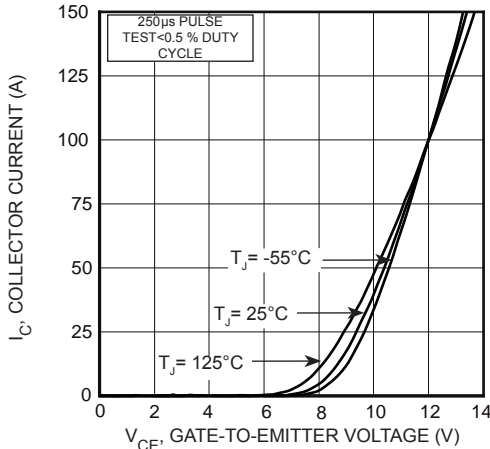


FIGURE 3, Transfer Characteristics

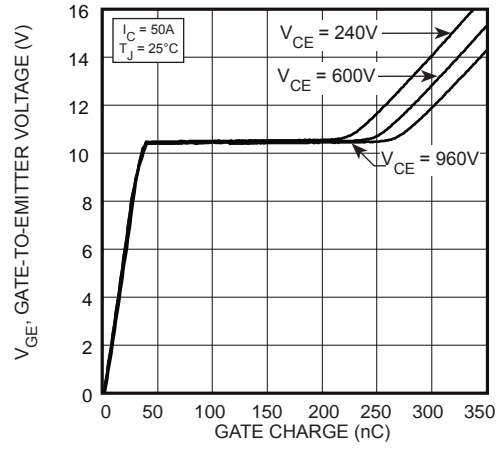


FIGURE 4, Gate charge

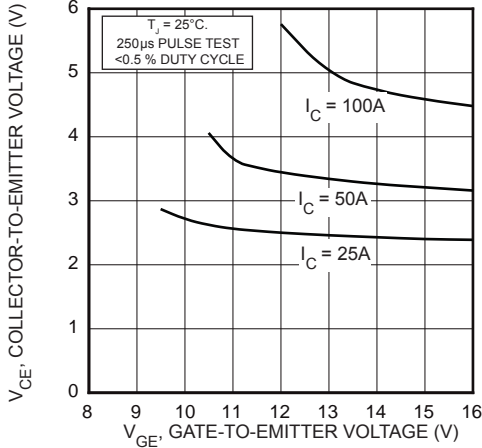


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

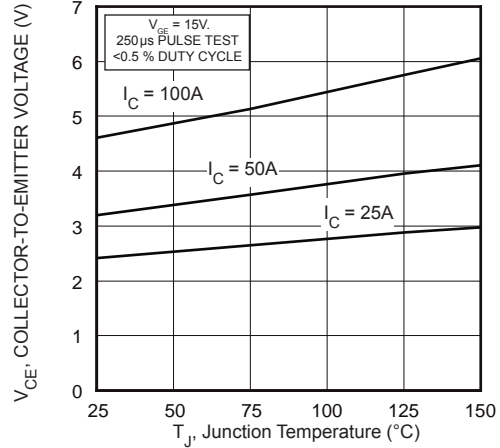


FIGURE 6, On State Voltage vs Junction Temperature

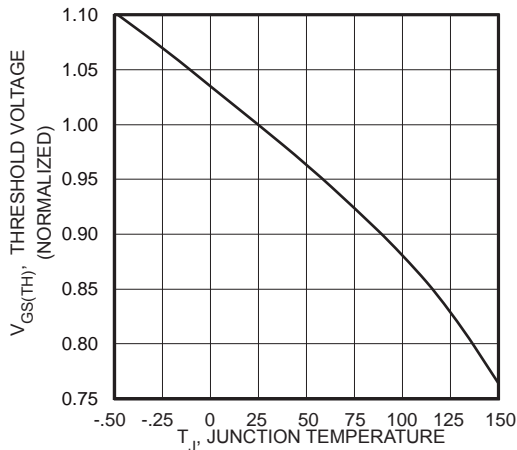


FIGURE 7, Threshold Voltage vs Junction Temperature

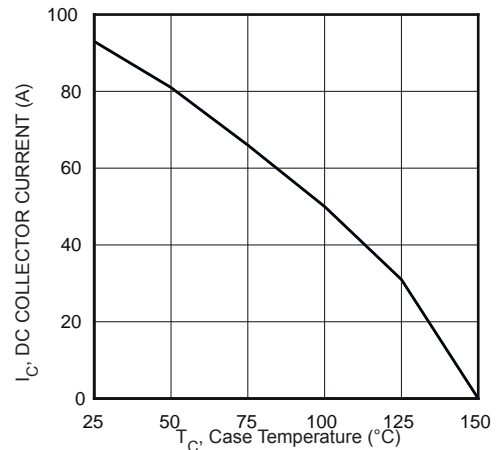


FIGURE 8, DC Collector Current vs Case Temperature

Typical Performance Curves

APT50GT120B2RDQ2G

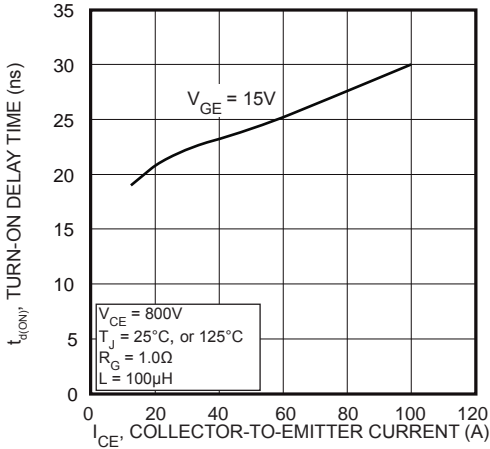


FIGURE 9, Turn-On Delay Time vs Collector Current

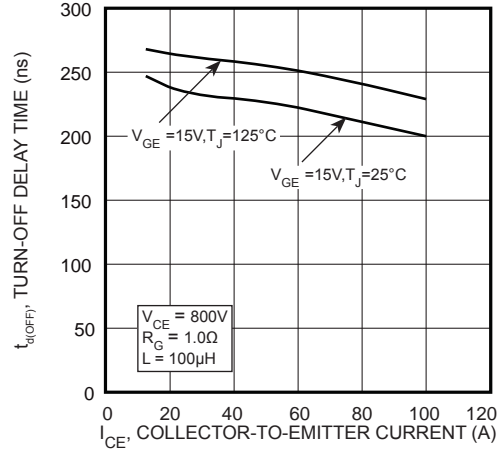


FIGURE 10, Turn-Off Delay Time vs Collector Current

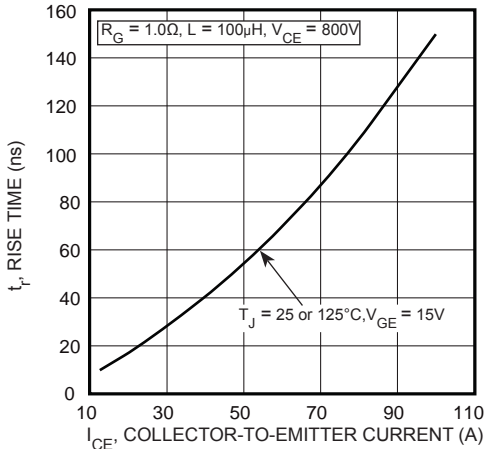


FIGURE 11, Current Rise Time vs Collector Current

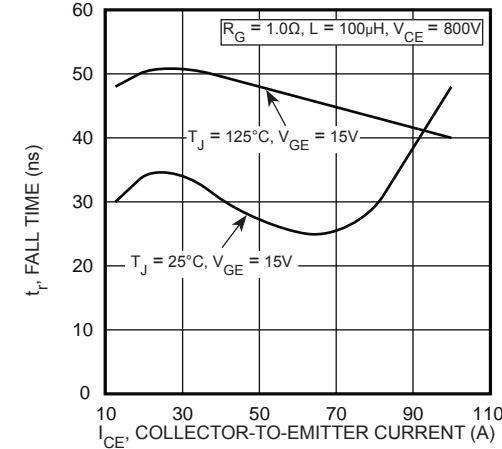


FIGURE 12, Current Fall Time vs Collector Current

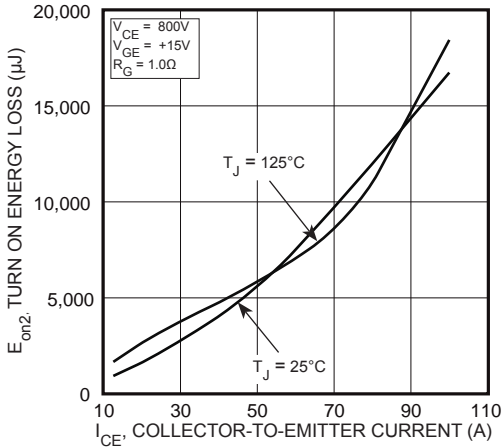


FIGURE 13, Turn-On Energy Loss vs Collector Current

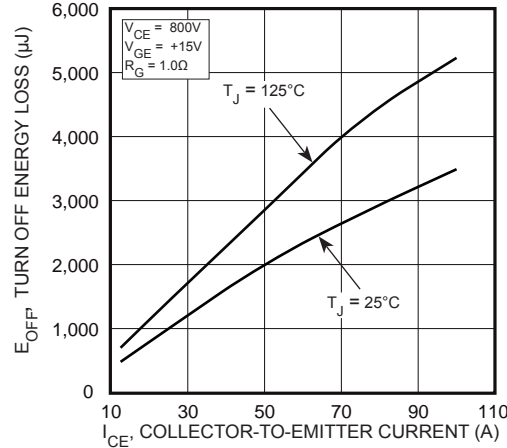


FIGURE 14, Turn-Off Energy Loss vs Collector Current

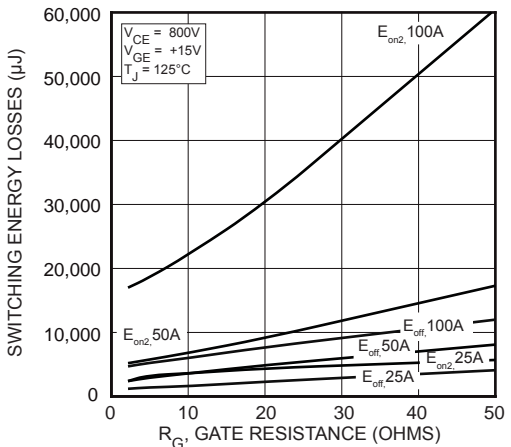


FIGURE 15, Switching Energy Losses vs Gate Resistance

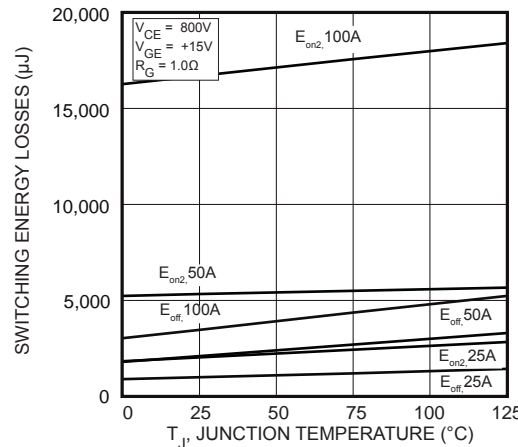


FIGURE 16, Switching Energy Losses vs Junction Temperature

Typical Performance Curves

APT50GT120B2RDQ2G

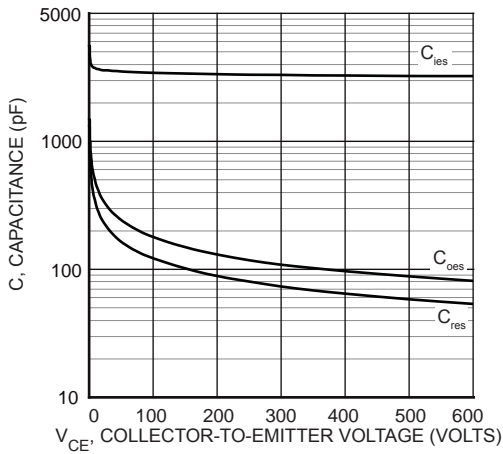


FIGURE 17, Capacitance vs Collector-To-Emitter Voltage

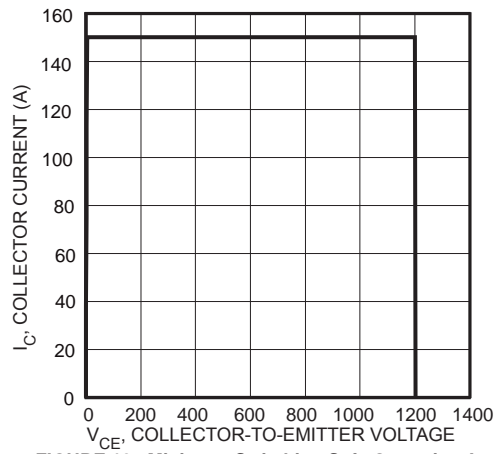


FIGURE 18, Minimum Switching Safe Operating Area

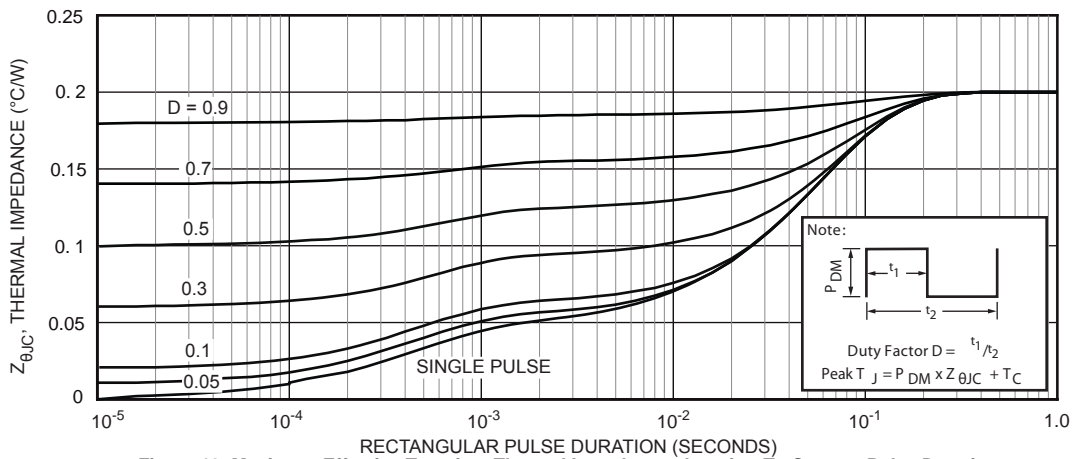


Figure 19, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

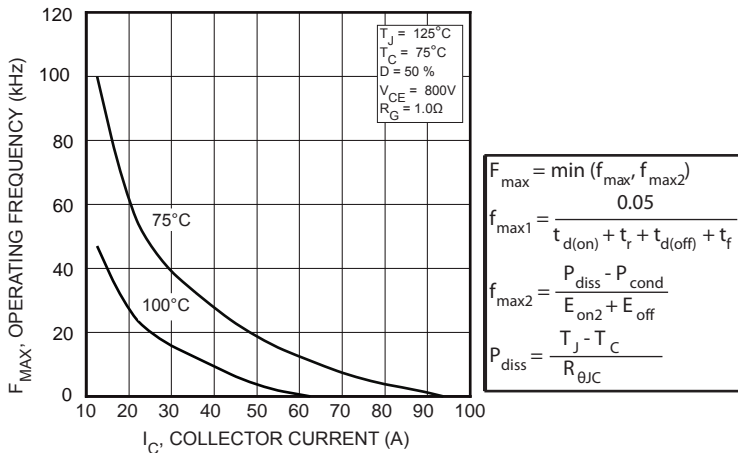


Figure 20, Operating Frequency vs Collector Current

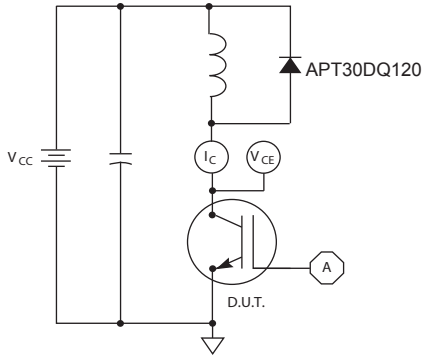


Figure 21, Inductive Switching Test Circuit

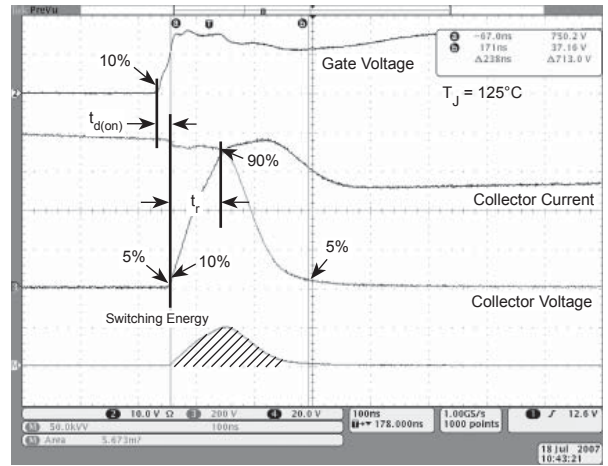


Figure 22, Turn-on Switching Waveforms and Definitions

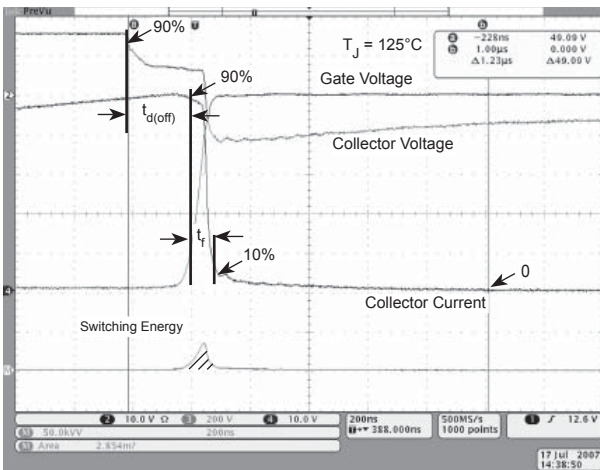


Figure 23, Turn-off Switching Waveforms and Definitions

ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT50GT120B2RDQ2G	Unit
$I_{F(AV)}$	Maximum Average Forward Current ($T_C = 103^\circ\text{C}$, Duty Cycle = 0.5)	30	Amps
$I_{F(RMS)}$	RMS Forward Current (Square wave, 50% duty)	43	
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3 ms)	210	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	Min	Type	Max	Unit	
V_F	Forward Voltage				Volts	
		$I_F = 30\text{A}$		2.8		3.3
		$I_F = 60\text{A}$		3.4		
	$I_F = 30\text{A}, T_J = 125^\circ\text{C}$		2.1			

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
t_{rr}	Reverse Recovery Time	$I_F = 1\text{A}, di_F/dt = -100\text{A}/\mu\text{s}, V_R = 30\text{V}, T_J = 25^\circ\text{C}$	-	26	-	ns
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 667\text{V}, T_C = 25^\circ\text{C}$	-	320	-	ns
Q_{rr}	Reverse Recovery Charge		-	545	-	nC
I_{RRM}	Maximum Reverse Recovery Current		-	4	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -200\text{A}/\mu\text{s}, V_R = 667\text{V}, T_C = 125^\circ\text{C}$	-	435	-	ns
Q_{rr}	Reverse Recovery Charge		-	2100	-	nC
I_{RRM}	Maximum Reverse Recovery Current		-	9	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}, di_F/dt = -1000\text{A}/\mu\text{s}, V_R = 800\text{V}, T_C = 125^\circ\text{C}$	-	180	-	ns
Q_{rr}	Reverse Recovery Charge		-	2975	-	nC
I_{RRM}	Maximum Reverse Recovery Current		-	28	-	Amps

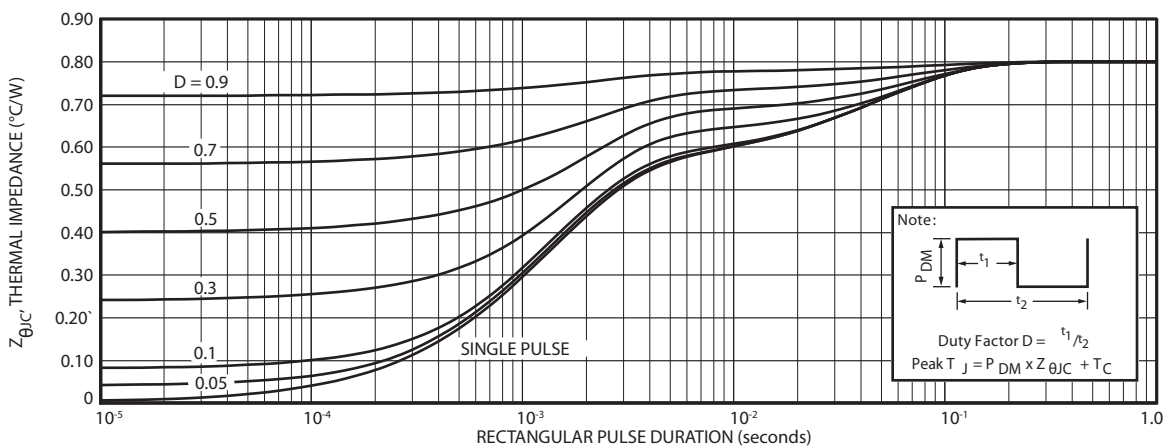


FIGURE 24. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

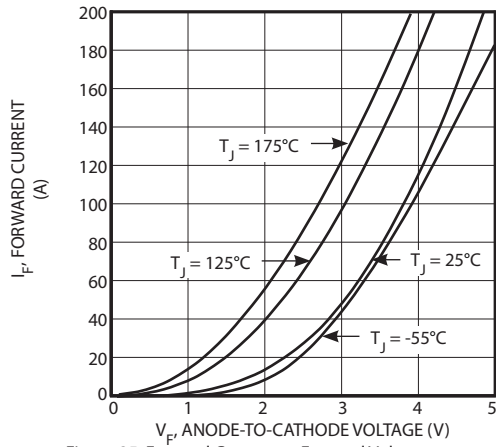


Figure 25. Forward Current vs. Forward Voltage

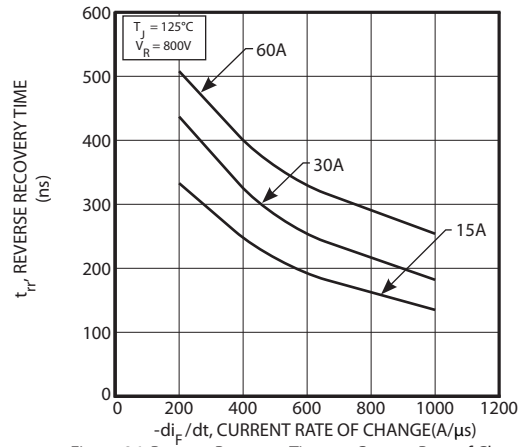


Figure 26. Reverse Recovery Time vs. Current Rate of Change

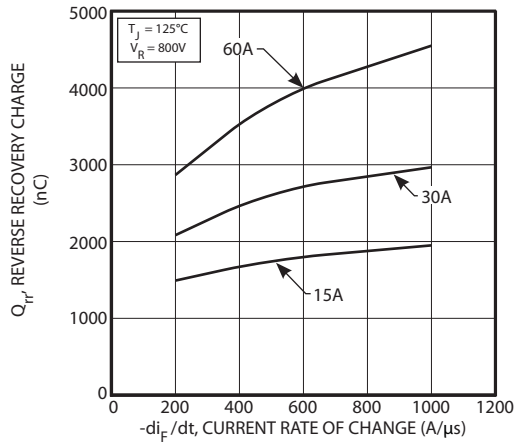


Figure 27. Reverse Recovery Charge vs. Current Rate of Change

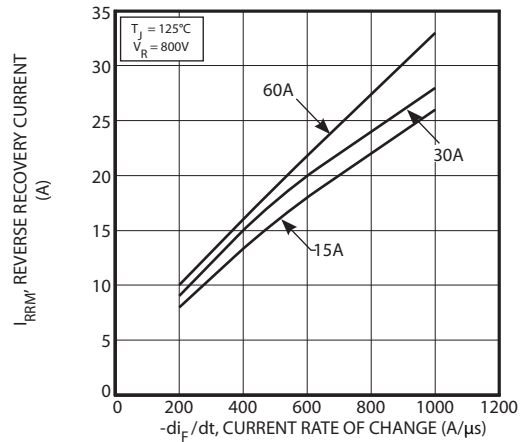


Figure 28. Reverse Recovery Current vs. Current Rate of Change

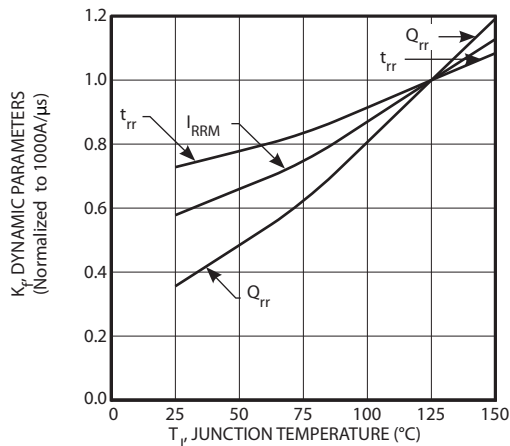


Figure 29. Dynamic Parameters vs. Junction Temperature

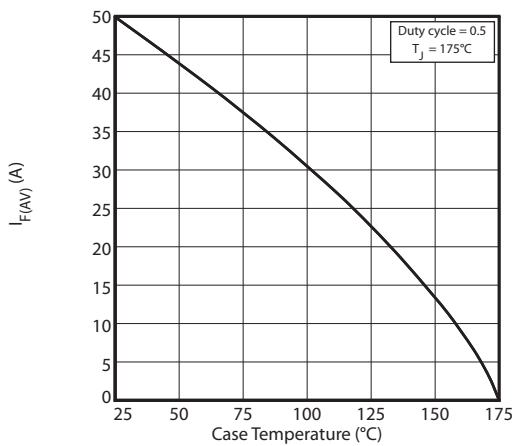


Figure 30. Maximum Average Forward Current vs. Case Temperature

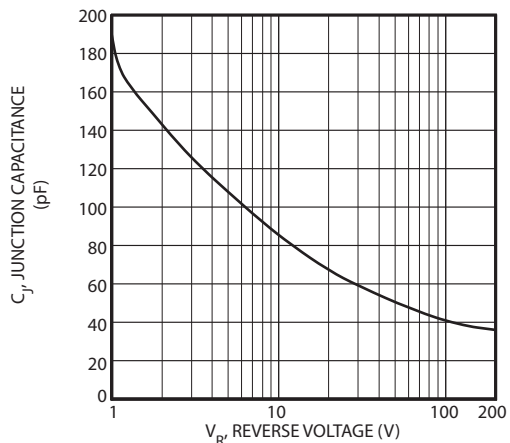


Figure 31. Junction Capacitance vs. Reverse Voltage

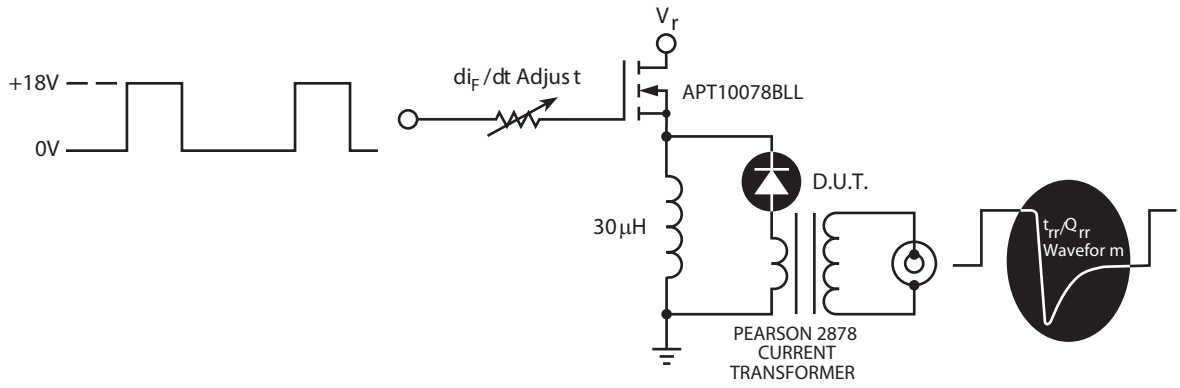


Figure 32. Diode Test Circuit

- 1 I_F - Forward Conduction Current
- 2 di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- 3 I_{RRM} - Maximum Reverse Recovery Current
- 4 t_{rr} - Reverse Recovery Time, measured from zero crossing where the diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 I_{RRM}$ passes through zero.
- 5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

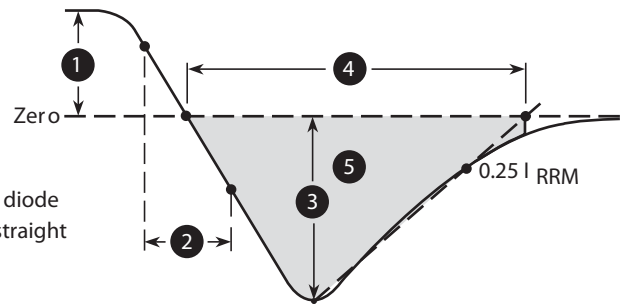
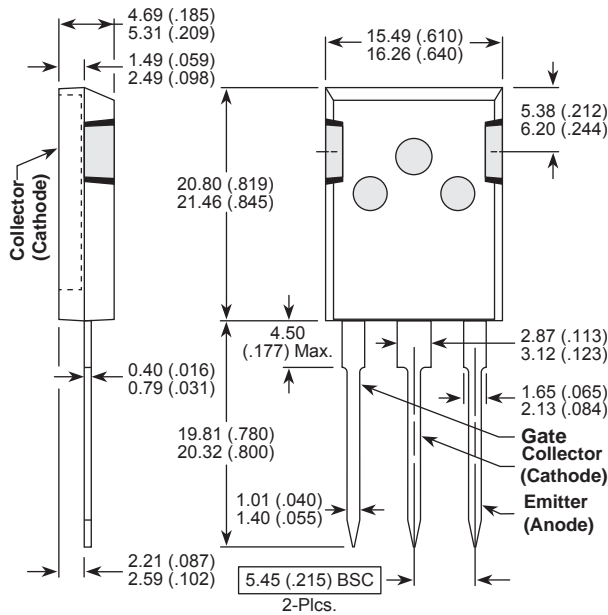


Figure 33, Diode Reverse Recovery Waveform and Definitions

T-MAX® Package Outline

(e1) SAC: Tin, Silver, Copper
(e3) 100% Sn



Dimensions in Millimeters and (Inches)

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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